

Serial No 09/008,531
Atty. Dkt. MIO 0012 V2/94-0012.04

- 2 -

AMENDMENTS TO THE CLAIMS

(The following includes a complete listing of all claims with their current status indicated.
Additional language is underscored; deletions are stricken through.)

21. (Currently Amended) A process for making a semiconductor device comprising the steps of:
 providing a substrate having at least one semiconductor layer;
 forming an underlayer having an opening over the at least one semiconductor layer;
 forming a layer of conductive material over the underlayer and in said opening, said layer of conductive material having a topography that includes a substantially vertical component in said opening;
 forming an overlayer over the said layer of conductive material said overlayer having a thickness greater than said underlayer;
 etching a contact hole in said overlayer and in an overetch amount of into but not through the substantially vertical component of said layer of conductive material in said opening; and
 forming a contact in said contact hole disposed adjacent to and directly contacting said vertical component.
22. (Original) A process as claimed in claim 21 wherein said vertical component defines a localized thick region in the layer of conductive material.
23. (Original) A process as claimed in claim 21 wherein said vertical component is a spacer.
24. (Original) A process as claimed in claim 21 further comprising the step of forming a structure having an opening therein under said conductive layer and filling said opening with said conductive material to form said vertical component.
25. (Original) A process as claimed in claim 21 wherein said conductive layer is a capacitor electrode.

Serial No 09/008,531
Atty. Dkt. MIO 0012 V2/94-0012.04

- 3 -

31. (Currently Amended) A process for making a semiconductor device comprising:

providing a substrate having at least one semiconductor layer;

forming a structure having an opening in said at least one semiconductor layer;

forming a layer of conductive material over said at least one semiconductor layer;

filling said opening with said conductive material to form a substantially vertical component in said opening;

forming an overlayer over said layer of conductive material, said overlayer having a thickness greater than said underlayer;

forming a contact hole in said overlayer and extending into said vertical component of said layer of conductive material, said contact hole disposed adjacent to and directly contacting said vertical component in said opening; and

filling said contact hole with a conducting material.

32. (Previously Presented) A process as claimed in claim 31 wherein said vertical component defines a localized thick region in the layer of conductive material.